

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	180	V
Collector-emitter voltage	V <sub>CEO</sub>	160	V
Emitter-base voltage	V <sub>EB0</sub>	6	V
Collector current-continuous	I <sub>c</sub>	0.6	A
Collector Power Dissipation	P <sub>c</sub>	625	mW
Junction and storage temperature	T <sub>J</sub> , T <sub>stg</sub>	- 5 5 t o + 1 5 0	°C

Collector-base breakdown voltage	V <sub>CB0</sub>	I <sub>c</sub> = 100 ìA, I <sub>E</sub> = 0	180		V
Collector-emitter breakdown voltage *	V <sub>CEO</sub>	I <sub>c</sub> = 1.0 mA, I <sub>B</sub> = 0	160		V
Emitter-base breakdown voltage	V <sub>EB0</sub>	I <sub>E</sub> = 10 ìA, I <sub>c</sub> = 0	6		V
Collector cutoff current	I <sub>CB0</sub>	V <sub>CB</sub> = 120 V, I <sub>E</sub> = 0		50	nA
Emitter cutoff current	I <sub>EB0</sub>	V <sub>EB</sub> = 4.0 V, I <sub>c</sub> = 0		50	nA
DC current gain *	h <sub>FE</sub>	I <sub>c</sub> = 1.0 mA, V <sub>CE</sub> = 5 V	80		
		I <sub>c</sub> = 10 mA, V <sub>CE</sub> = 5 V	80	250	
		I <sub>c</sub> = 50 mA, V <sub>CE</sub> = 5 V	30		
Collector-emitter saturation voltage *	V <sub>CE(sat)</sub>	I <sub>c</sub> = 10 mA, I <sub>B</sub> = 1 mA		0.15	V
		I <sub>c</sub> = 50 mA, I <sub>B</sub> = 5mA		0.2	
Base-emitter saturation voltage *	V <sub>BE(sat)</sub>	I <sub>c</sub> = 10 mA, I <sub>B</sub> = 1 mA		1.0	V
		I <sub>c</sub> = 50 mA, I <sub>B</sub> = 5 mA		1.0	
Transiston frequency	f <sub>t</sub>	V <sub>CE</sub> =10V, I <sub>c</sub> =10mA, f=100MHz	100	300	MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		6	pF
Input capacitance	C <sub>ib</sub>	V <sub>BE</sub> =0.5V, I <sub>c</sub> =0, f=1MHz		20	pF
Noise figure	NF	V <sub>CE</sub> =5V, I <sub>c</sub> =0.25mA, f=10Hz to 15.7KHz, R <sub>s</sub> =1k <sub>Ω</sub>			

\* Pulse Test: Pulse Width = 300 μs, Duty Cycle=2.0%.